

FIG. 1A

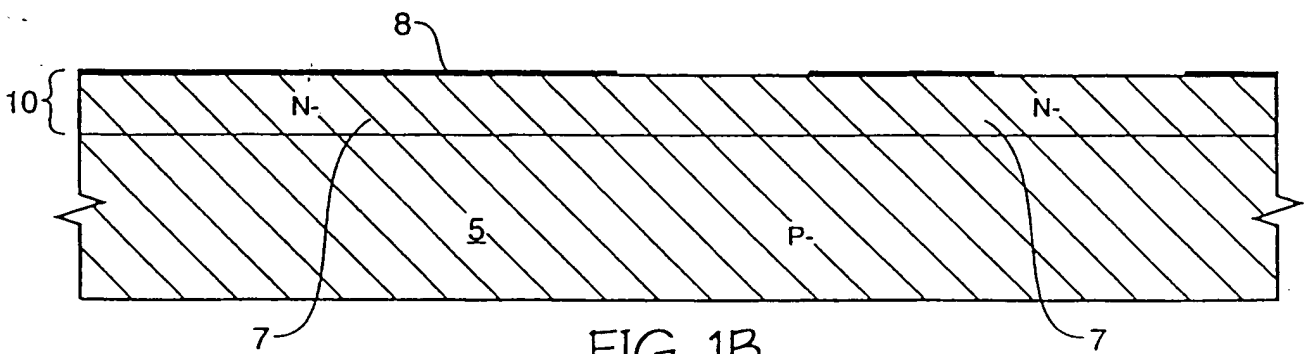


FIG. 1B





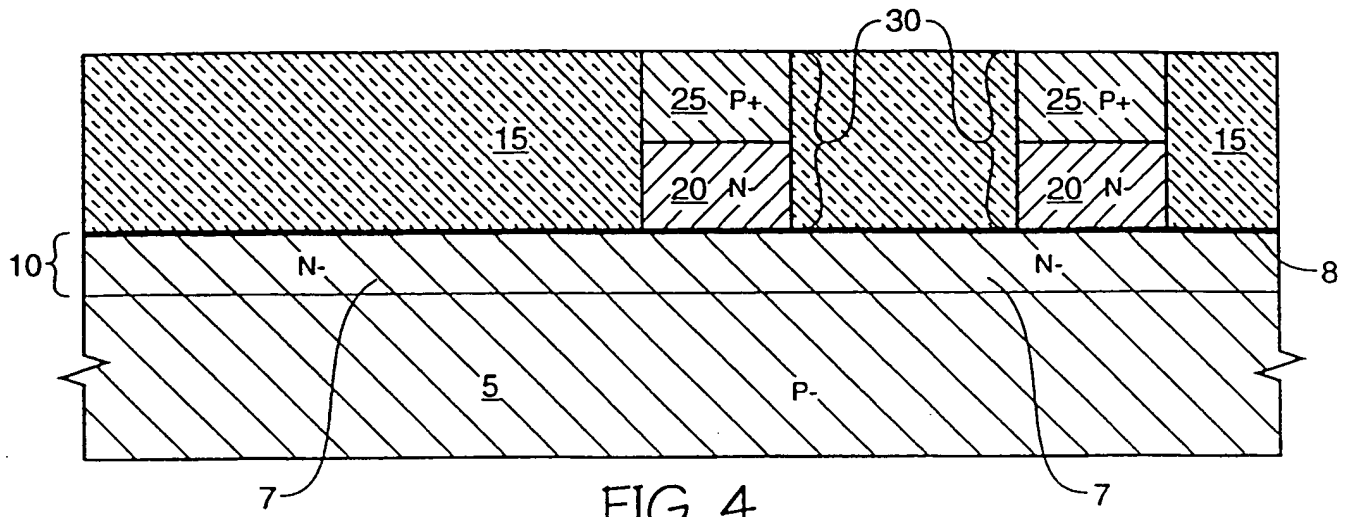


FIG. 4

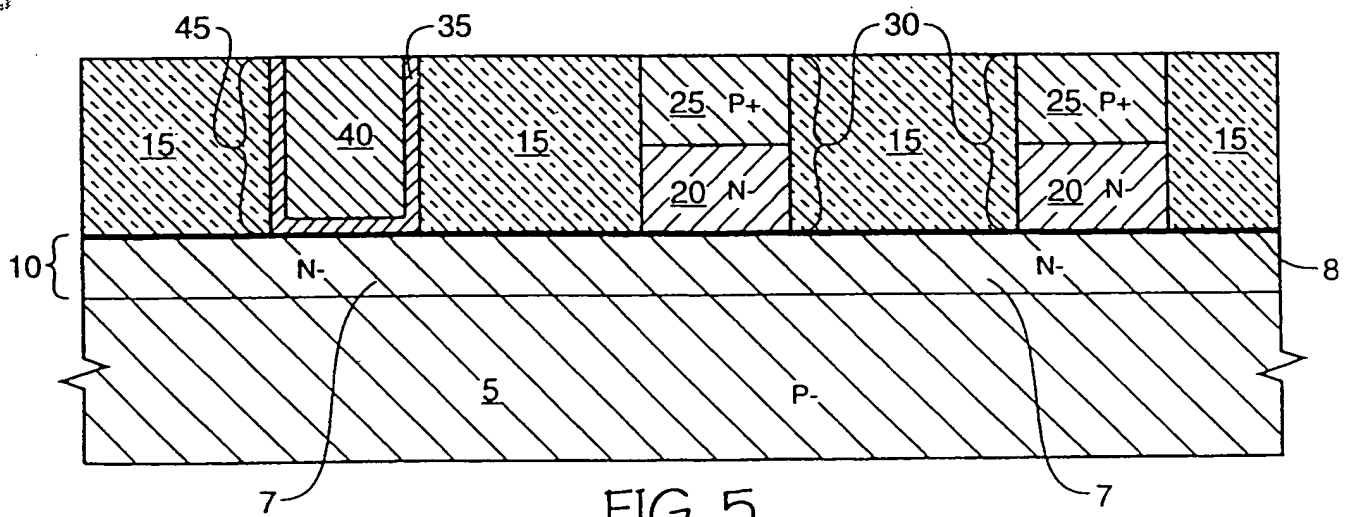


FIG. 5

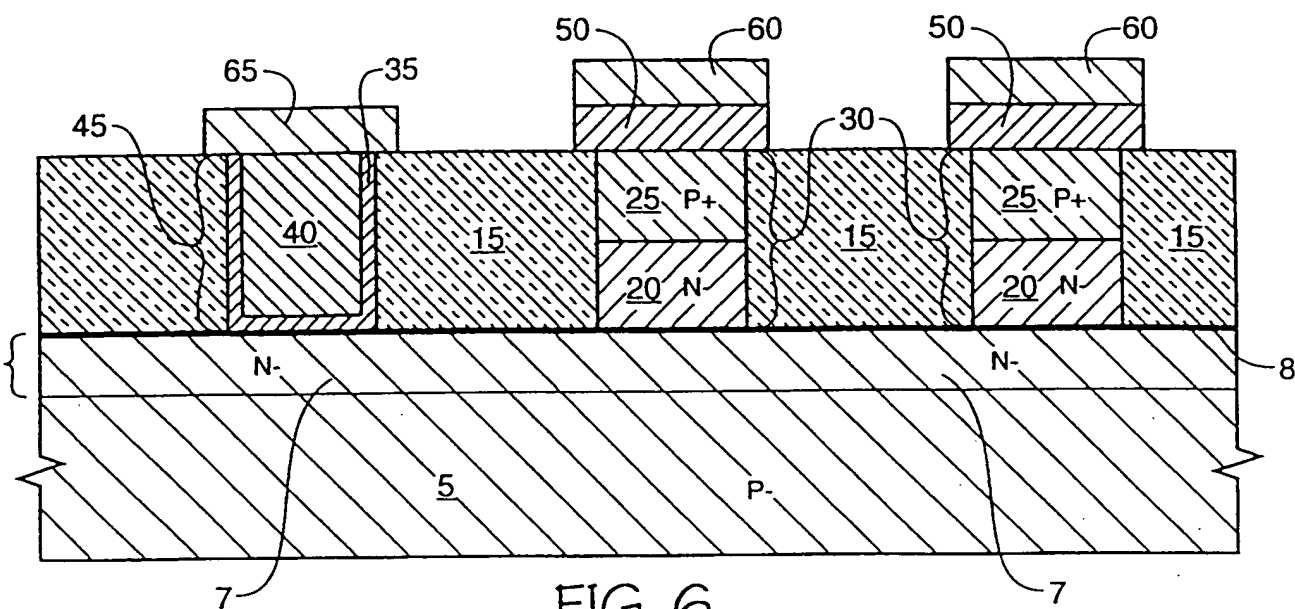


FIG. 6

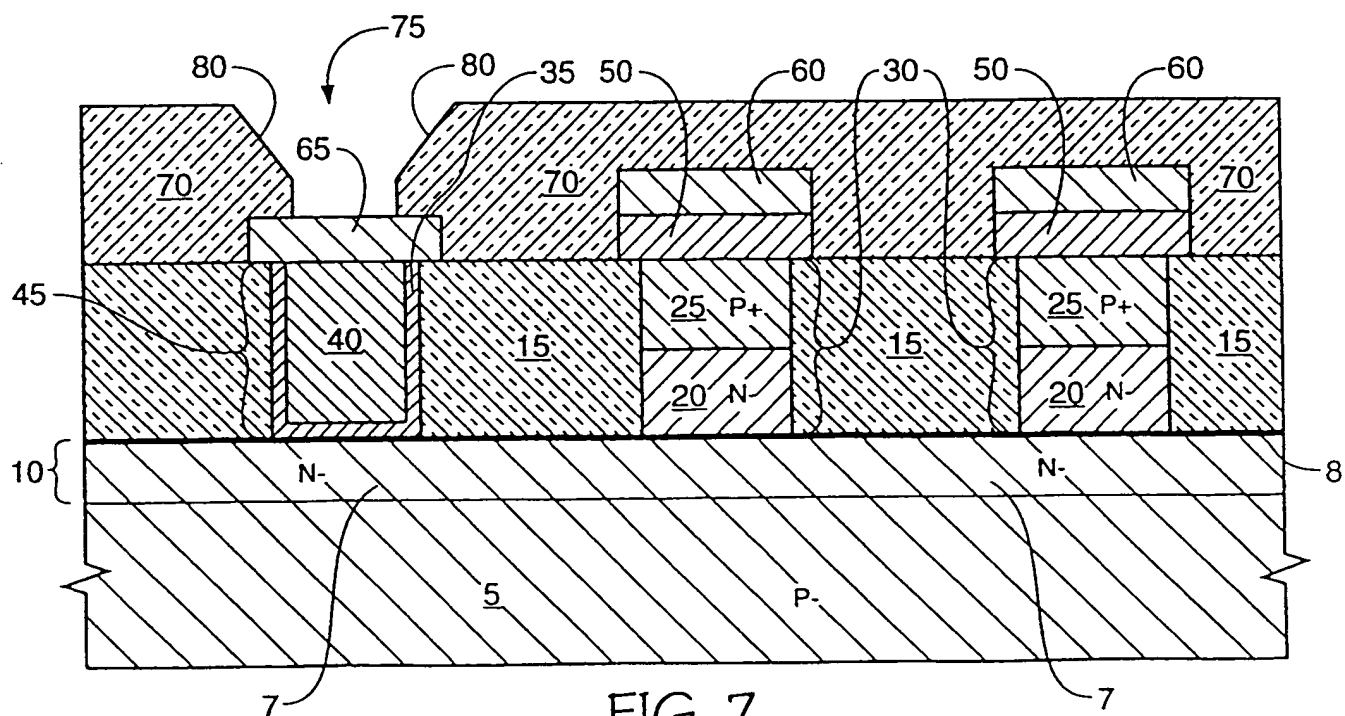


FIG. 7

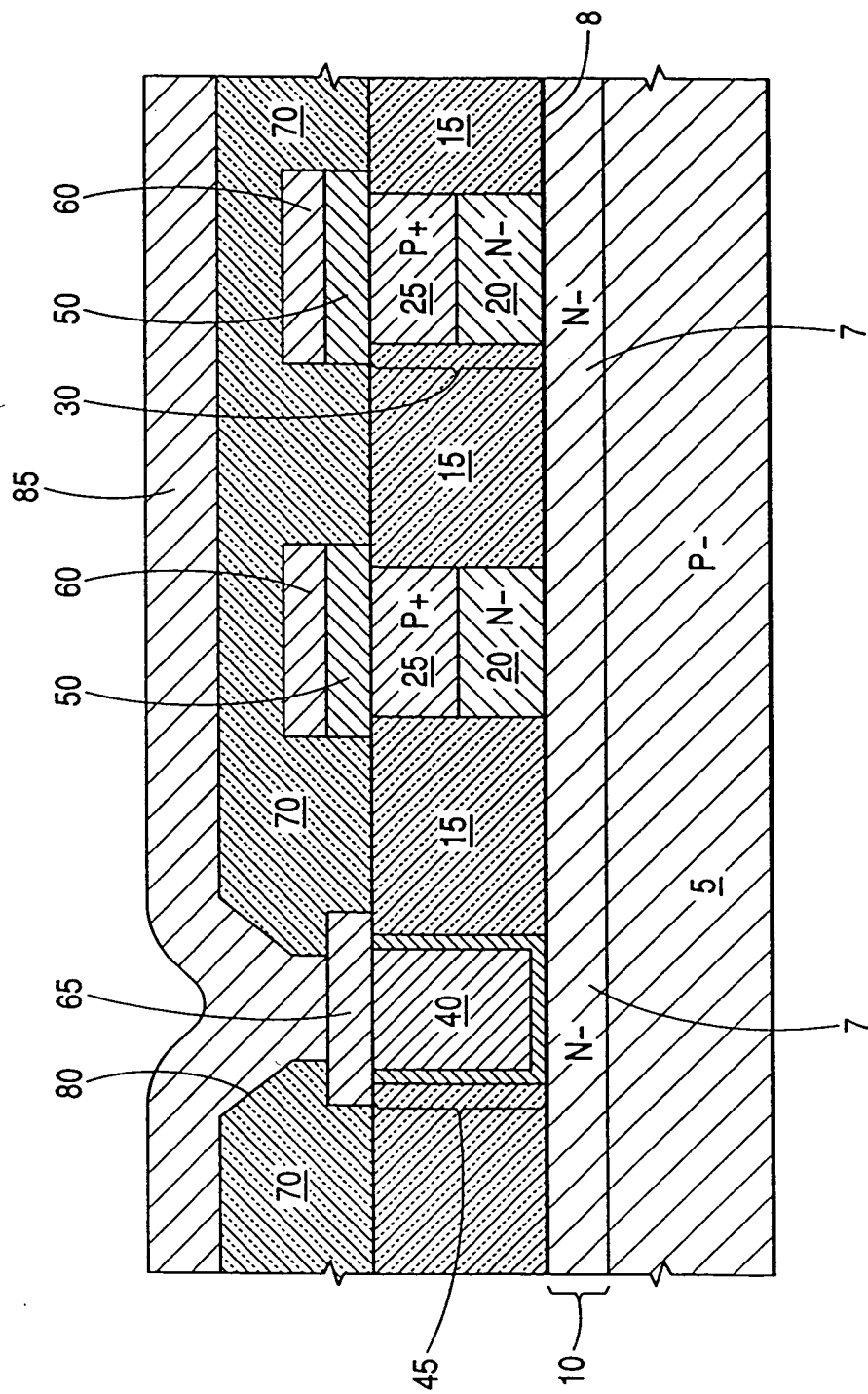
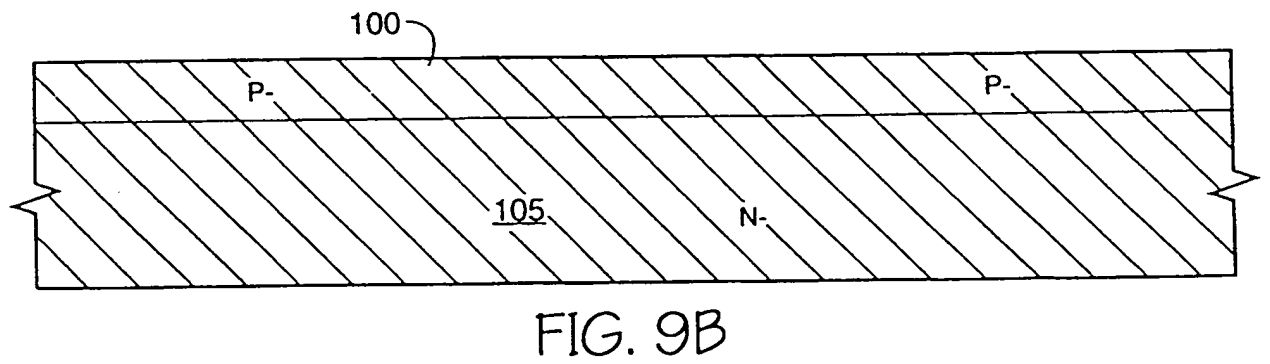
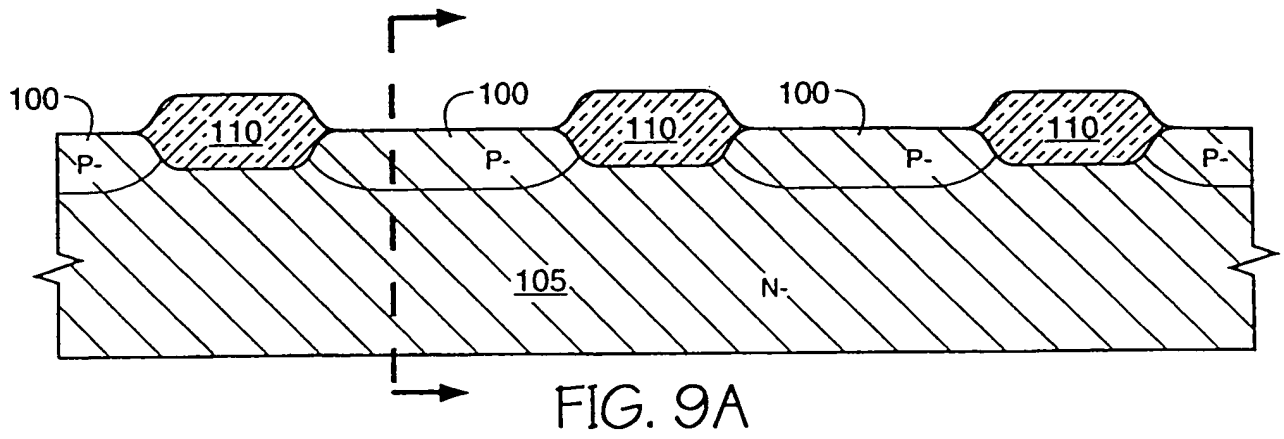


FIG. 8



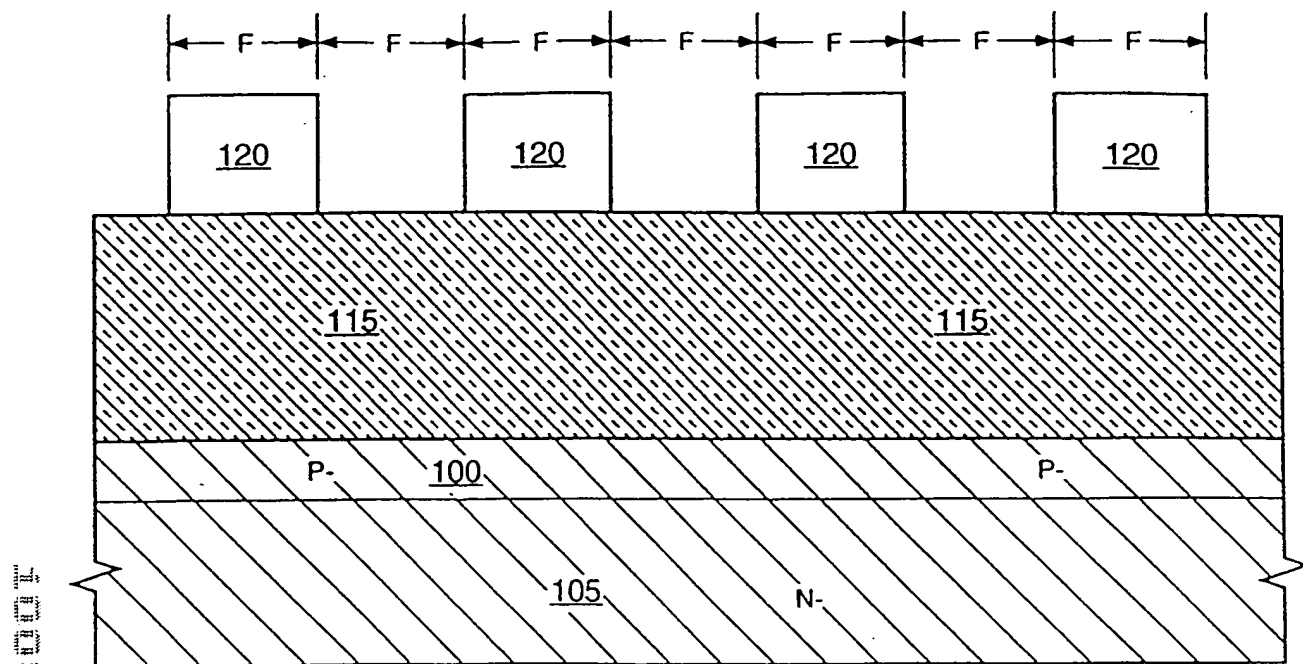


FIG. 10A

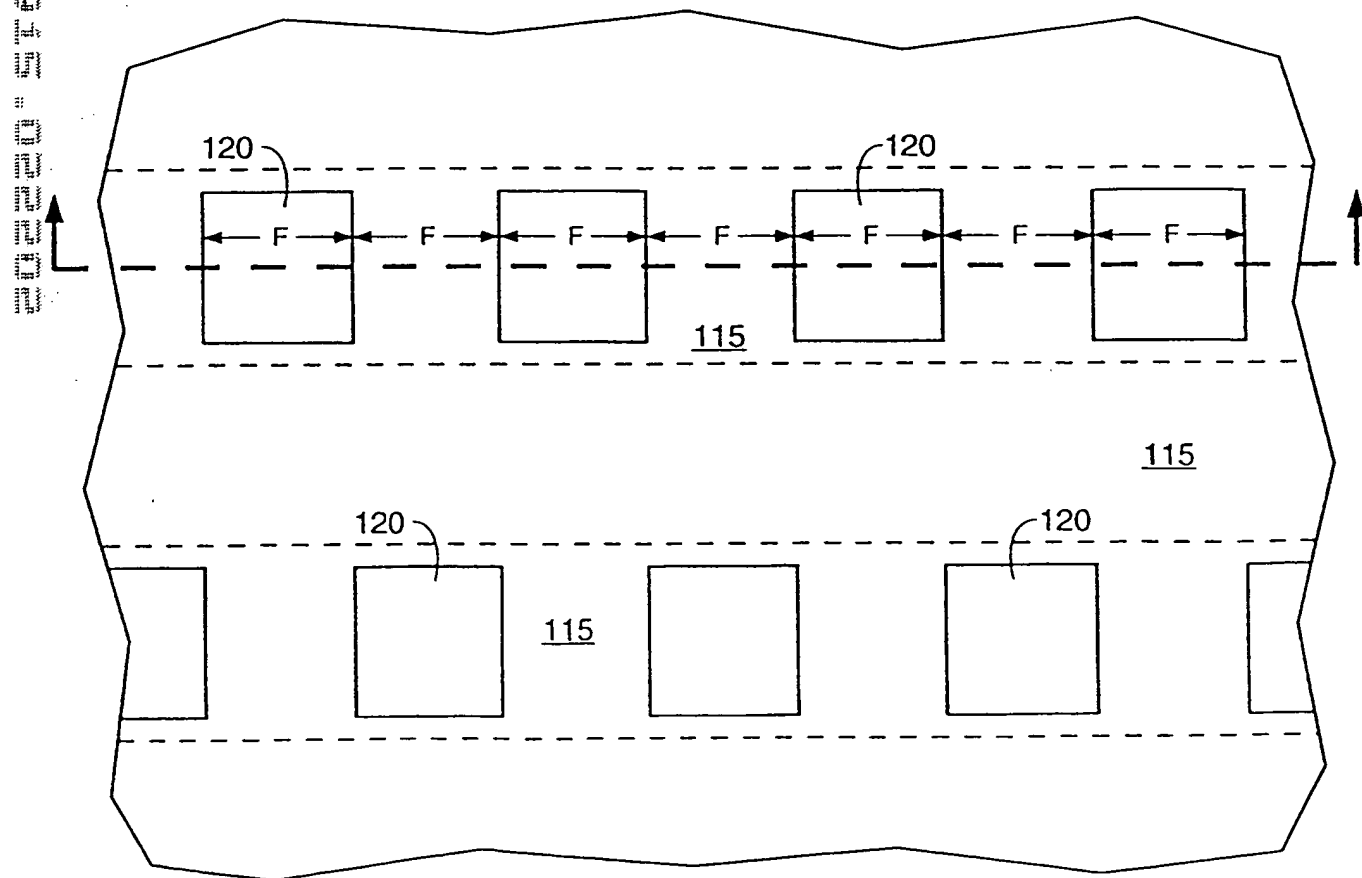


FIG. 10B



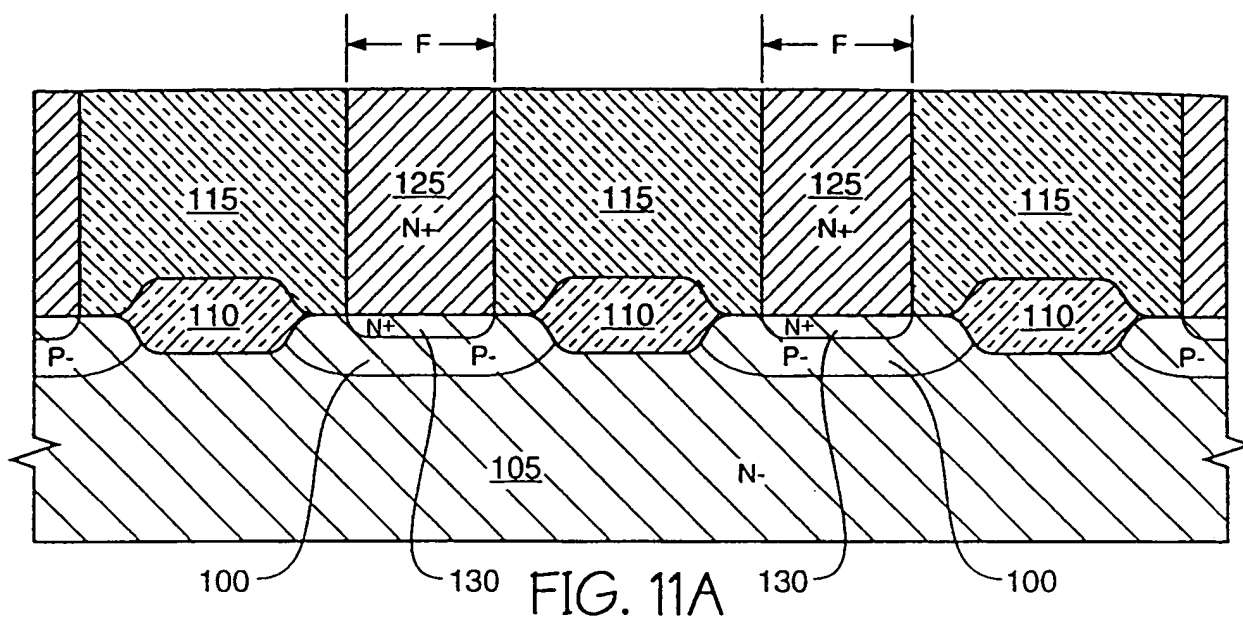


FIG. 11A

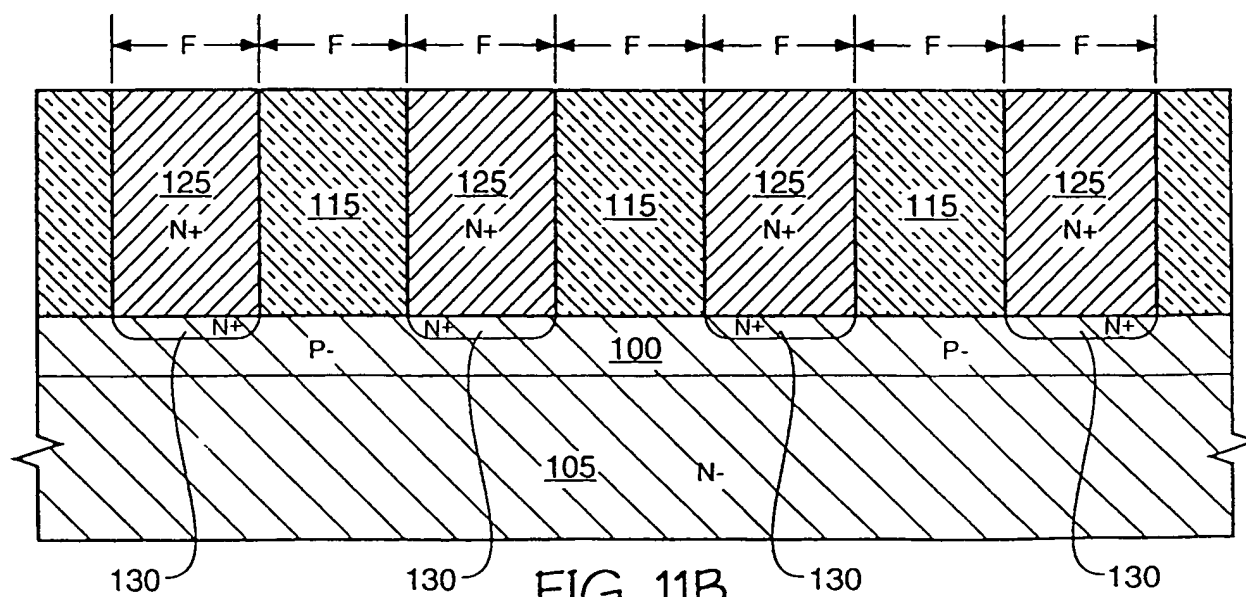


FIG. 11B

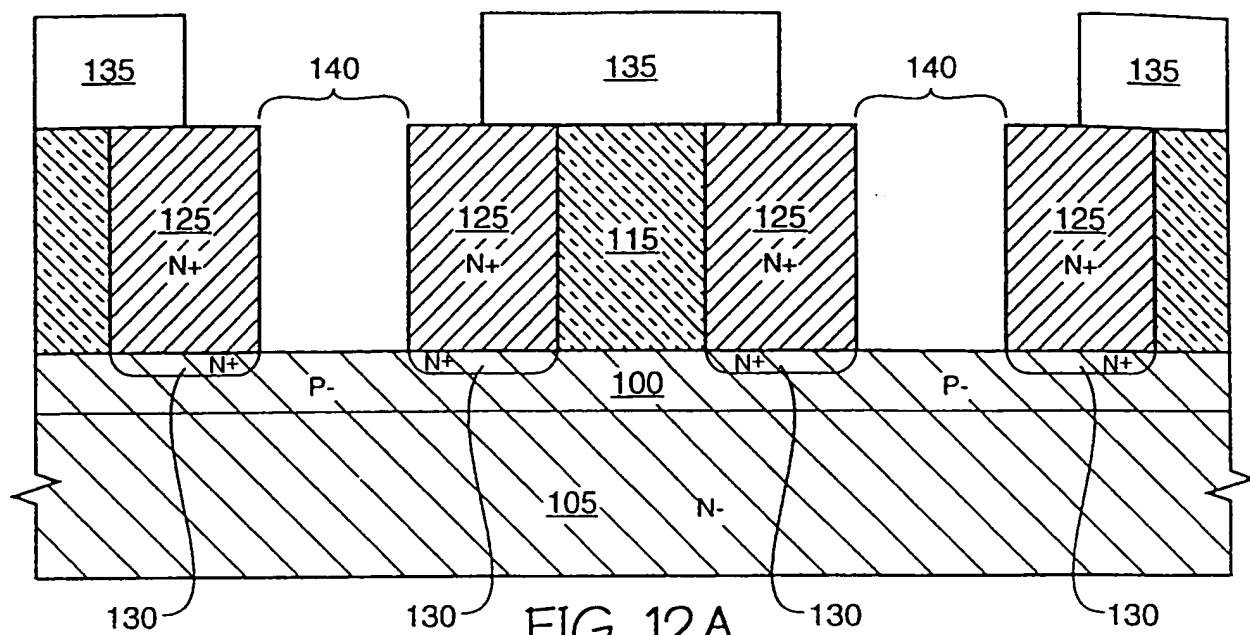


FIG. 12A

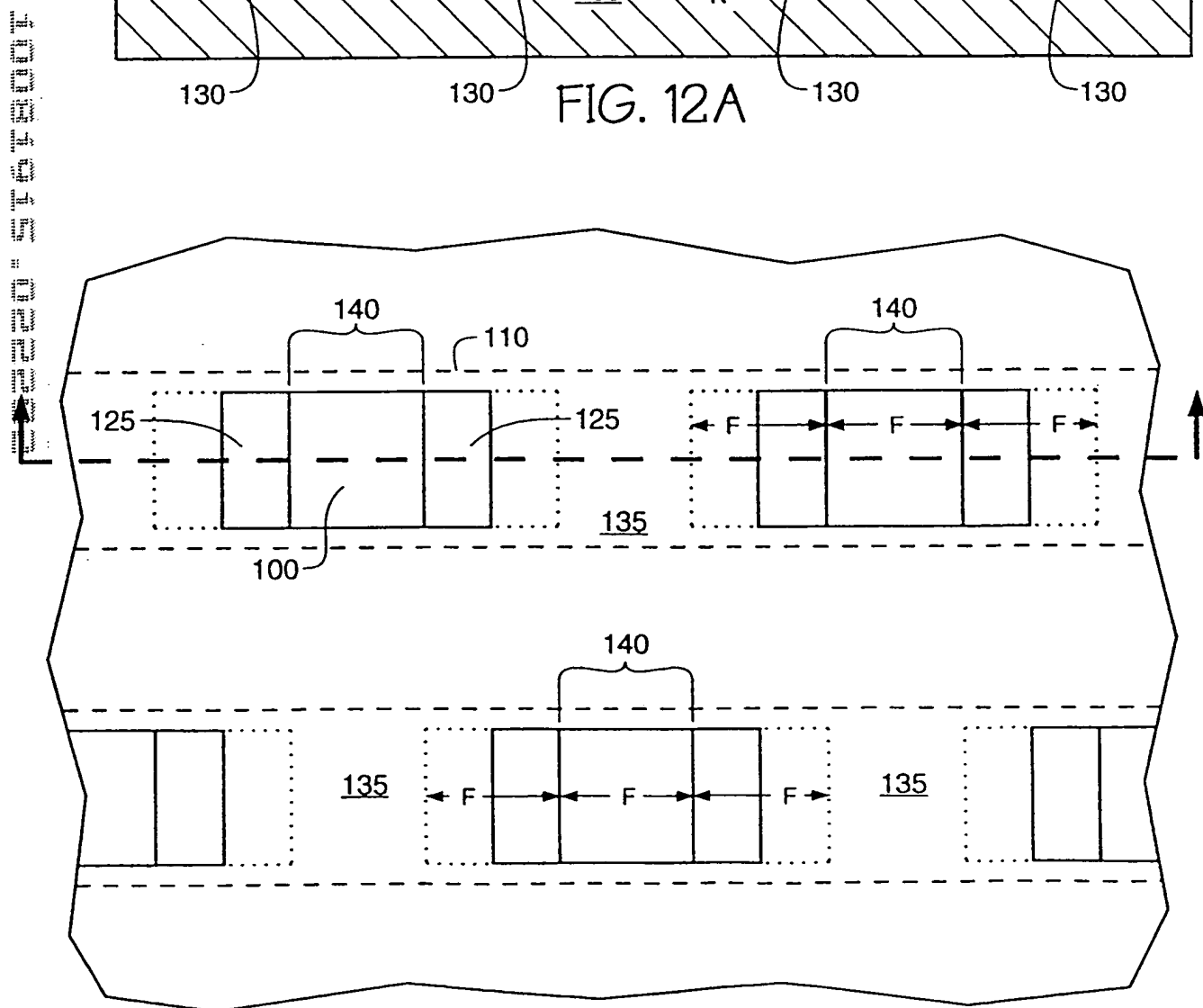


FIG. 12B

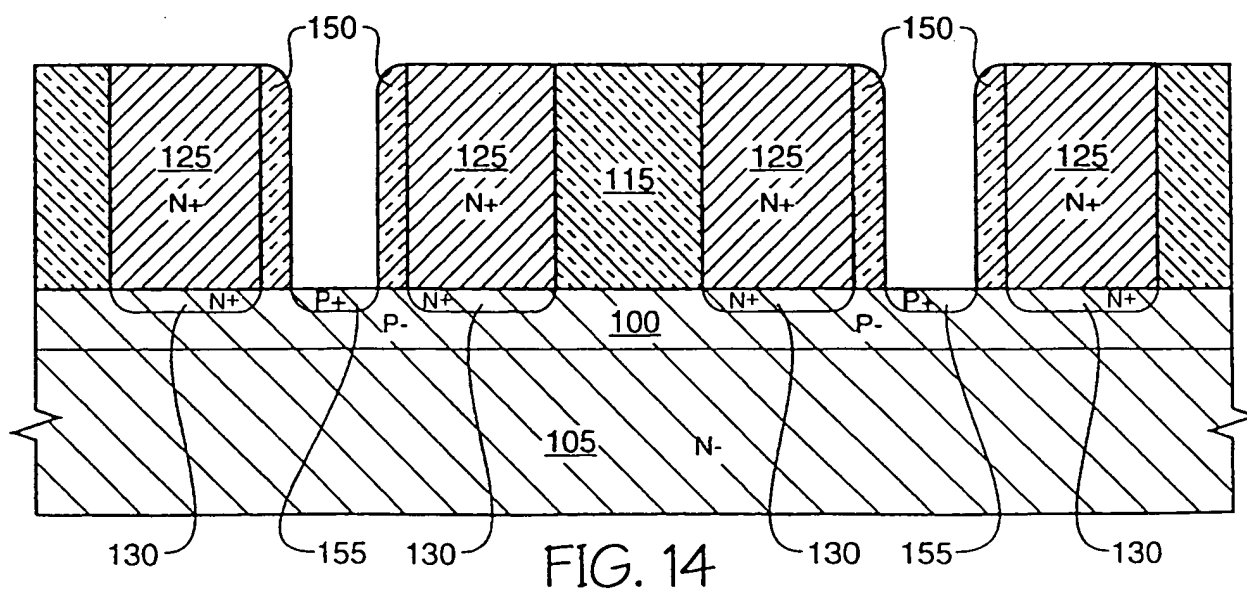
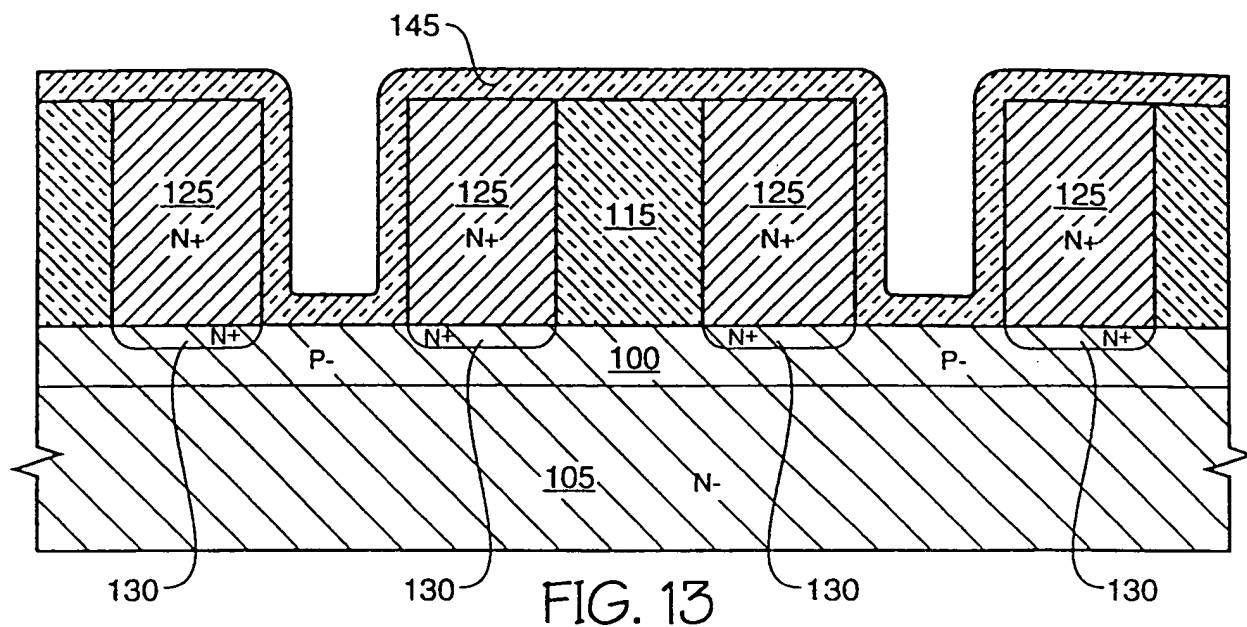


FIG. 15 is a cross-sectional view of a semiconductor device. The device includes a substrate 100 with a top layer 105. A series of regions are formed on the top layer 105, including N+ regions 125, P+ regions 155, and P- regions 130. A central region 115 is also shown. The regions are separated by a layer 150. The bottom layer 105 is labeled N-.

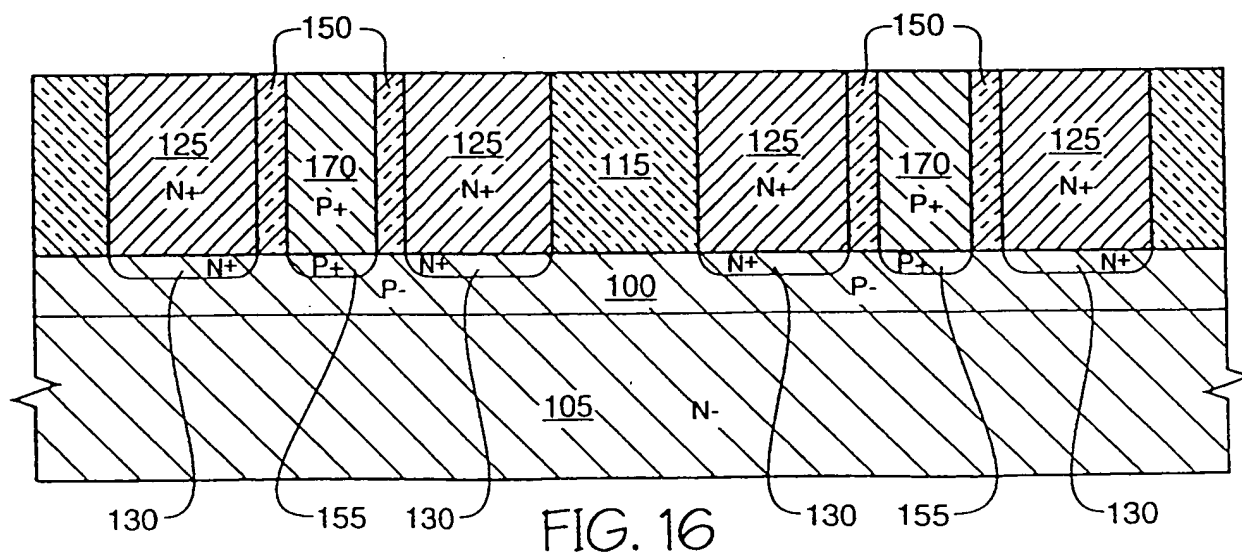


FIG. 17A

FIG. 17A

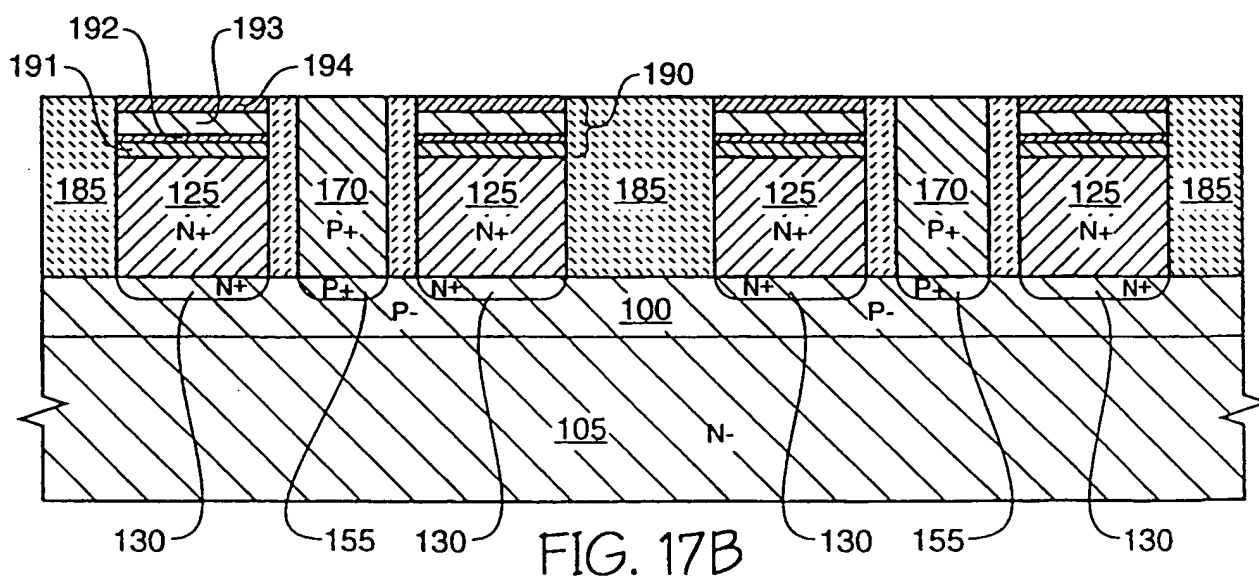


FIG. 17B

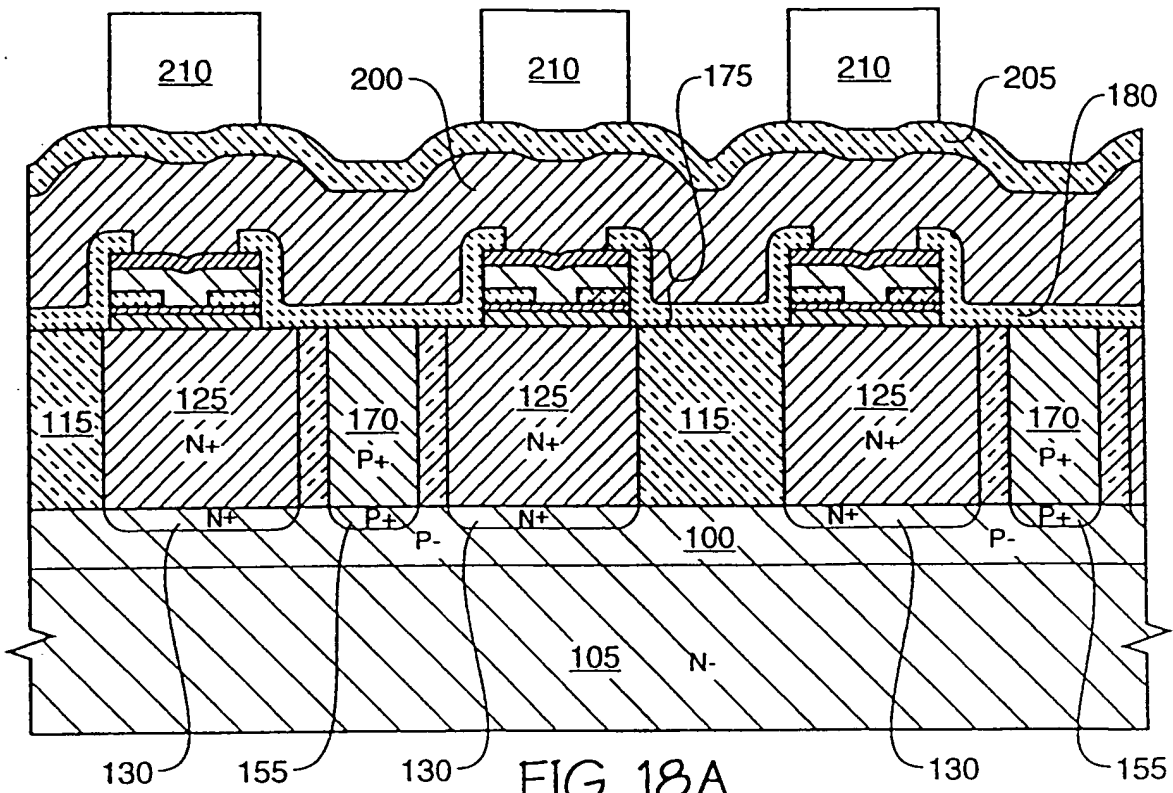


FIG. 18A

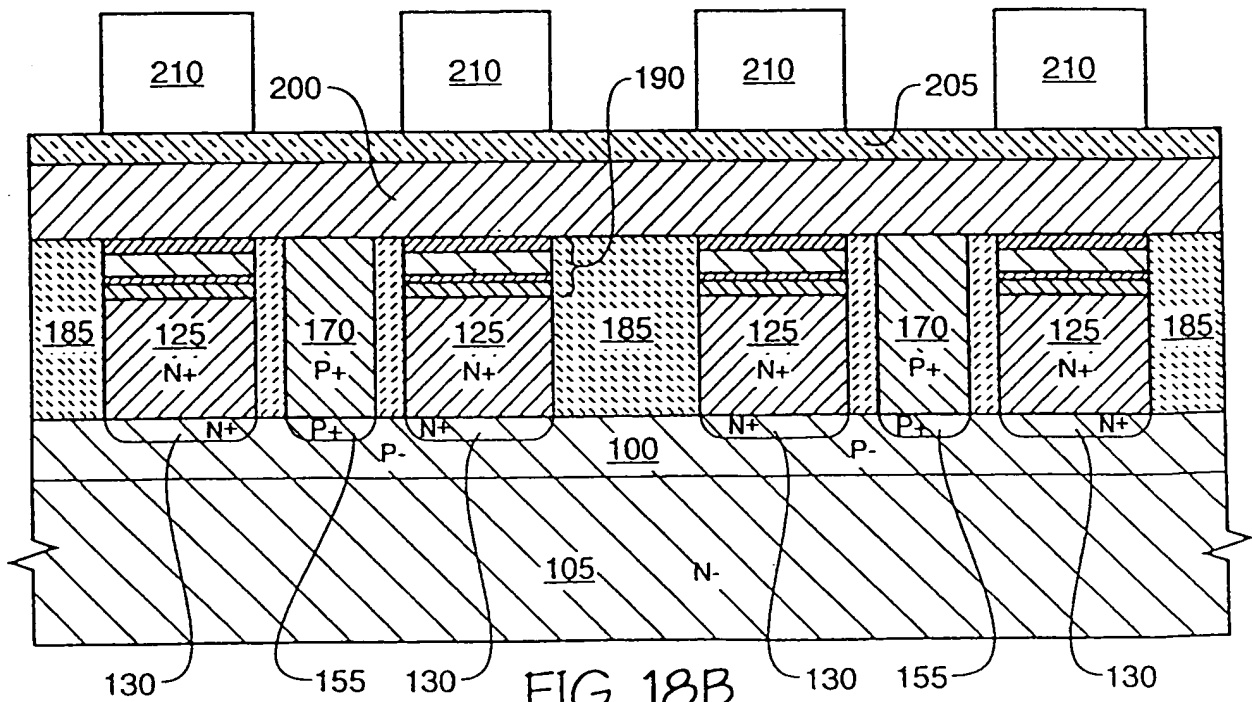


FIG. 18B

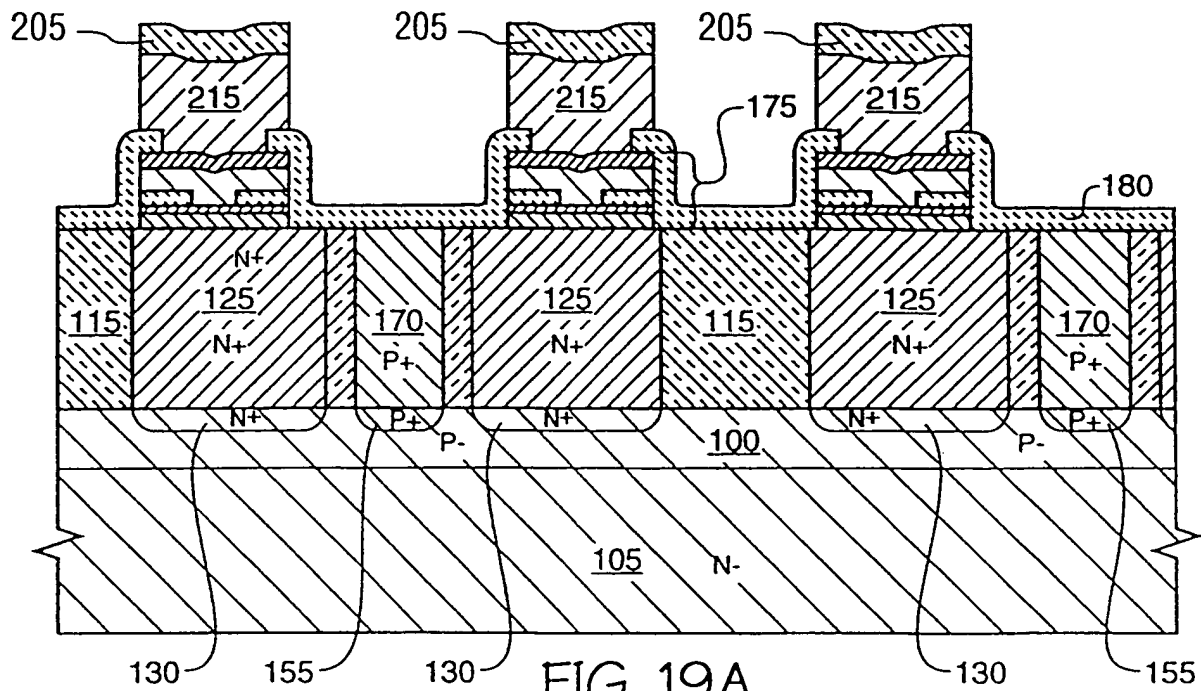


FIG. 19A

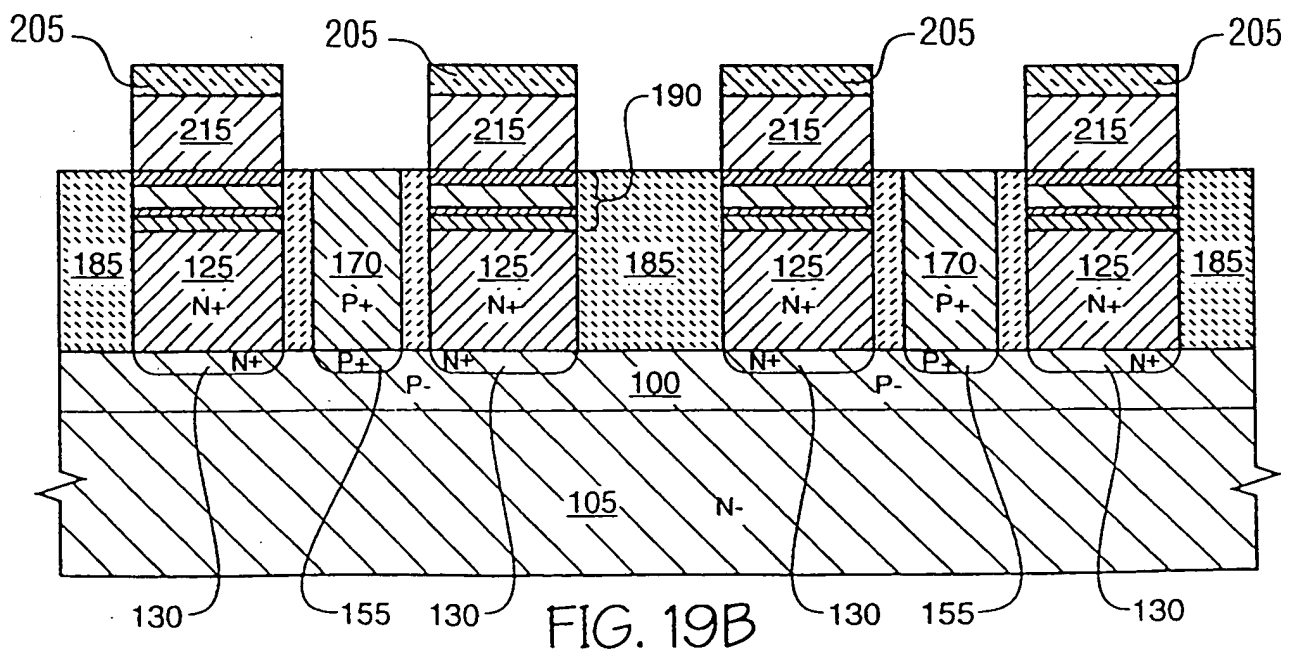


FIG. 19B

